

/ Descriptions

TO-252 N MOS

N-Channel Enhancement Mode Field Effect Transistor in a TO-252 Plastic Package.

/ Features

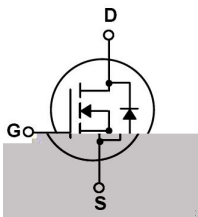
 $V_{DS} (V) = 30V$ $I_D = 135 A$ ($V_{GS} = \pm 20V$) $R_{DS(ON)}@10V$ 3mR(Typ.2.3mR) $R_{DS(ON)}@4.5V$ 5mR(Typ.3.1mR)

HF Product.

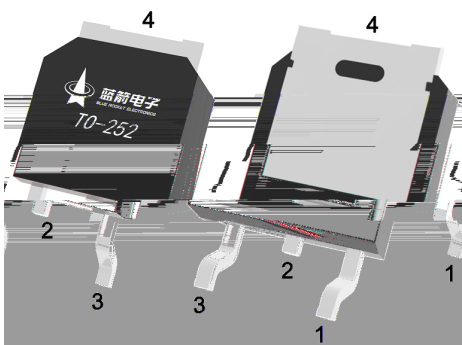
/ Applications

Load Switch Applications, Battery Power Management.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 4 D PIN 3 S

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25 °C)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Drain Current		$I_D(T_c=25^\circ\text{C})$	135	A
Drain Current - Pulsed		I_{DM}	285	A
Gate-Source Voltage		V_{GS}	± 20	V
Single Pulsed Avalanche Energy		E_{AS}	706	mJ
Avalanche Current		I_{AS}	42	A
Power Dissipation		$P_D(T_c=25^\circ\text{C})$	90	W
Operating and Storage Temperature Range		T_J, T_{stg}	-55 to 150	
Junction-to-Ambient	$t \leq 10$	R_{JA}	20	/W
Junction-to-Ambient	Steady-State		50	
Junction-to-Case	Steady-State	R_{JC}	1.39	

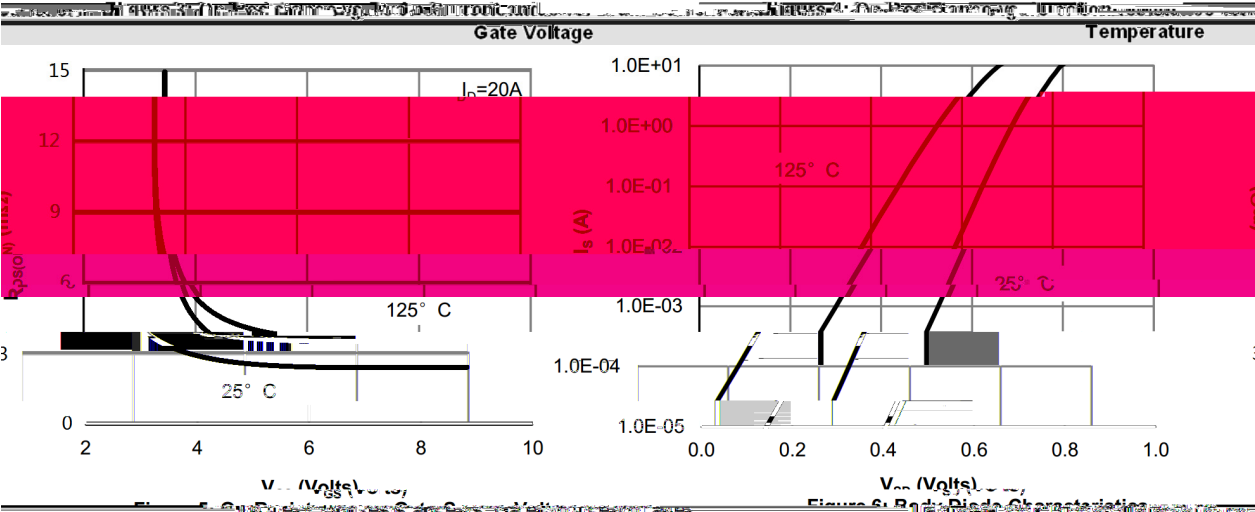
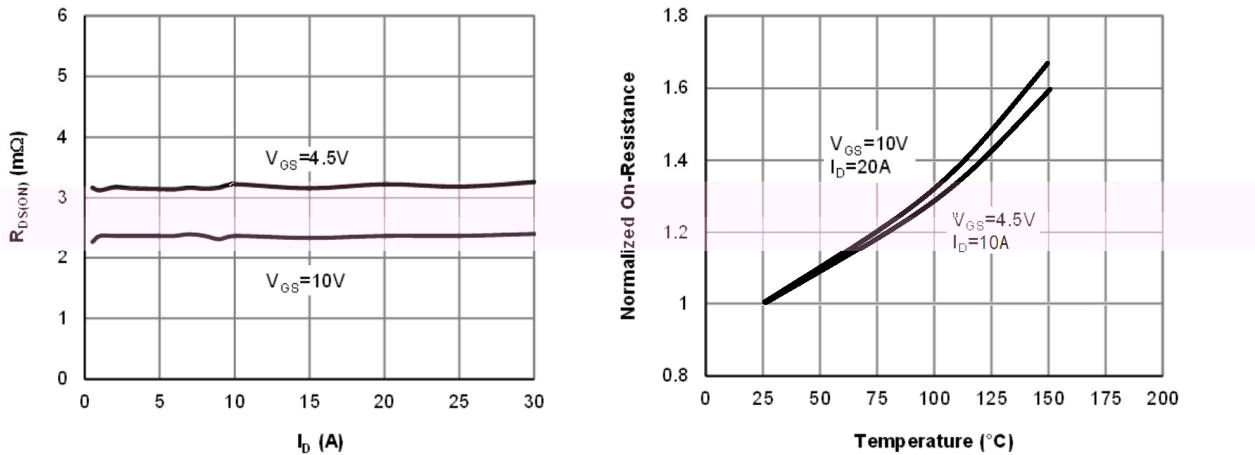
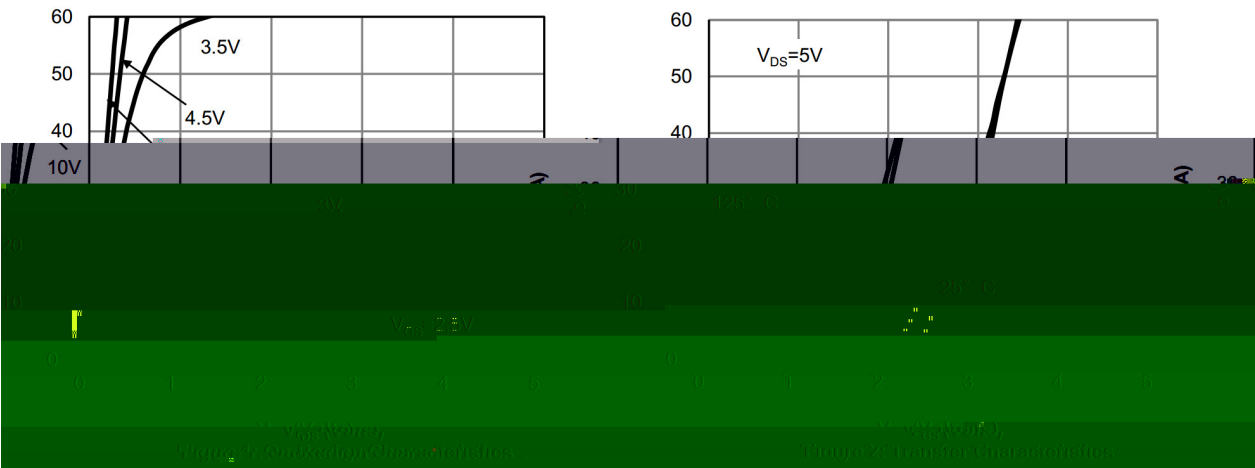
/ Electrical Characteristics(Ta=25 °C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\text{ A}$	30	35		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$ $V_{GS}=0V$			1	A
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	A
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\text{ A}$	1.0	1.6	3.0	V
Static Drain-Source On-Resistance	$R_{DS(on)1}$	$V_{GS}=10V$ $I_D=20A$		2.3	3	m
	$R_{DS(on)2}$	$V_{GS}=4.5V$ $I_D=10A$		3.1	5	m
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.2	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1MHz$		4650		pF
Output Capacitance	C_{oss}			650		
Reverse Transfer Capacitance	C_{rss}			480		
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		1.5		

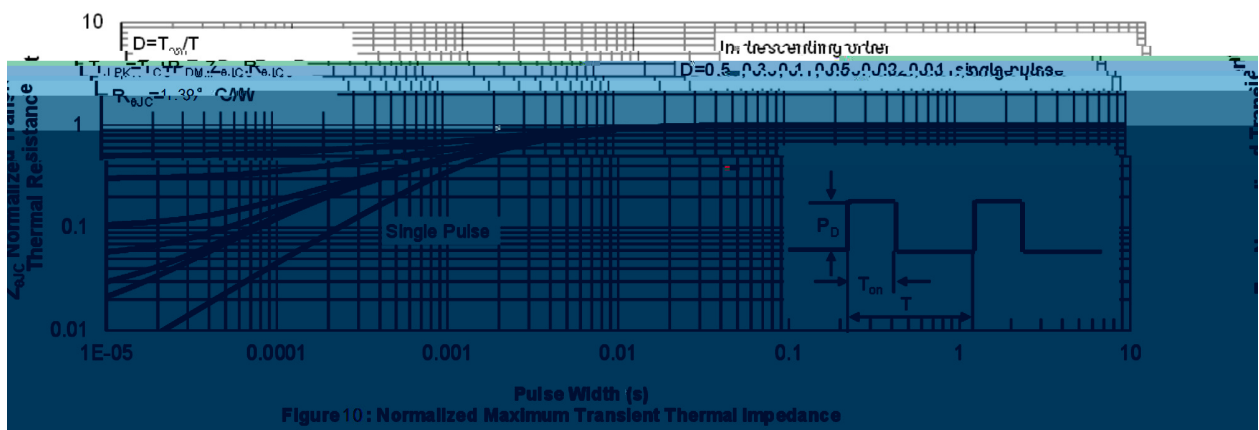
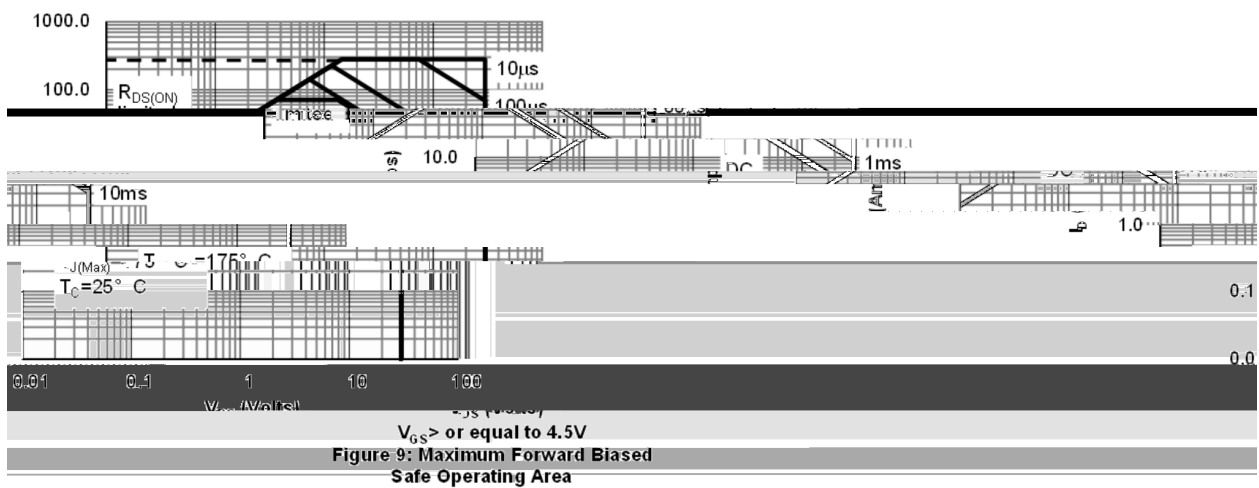
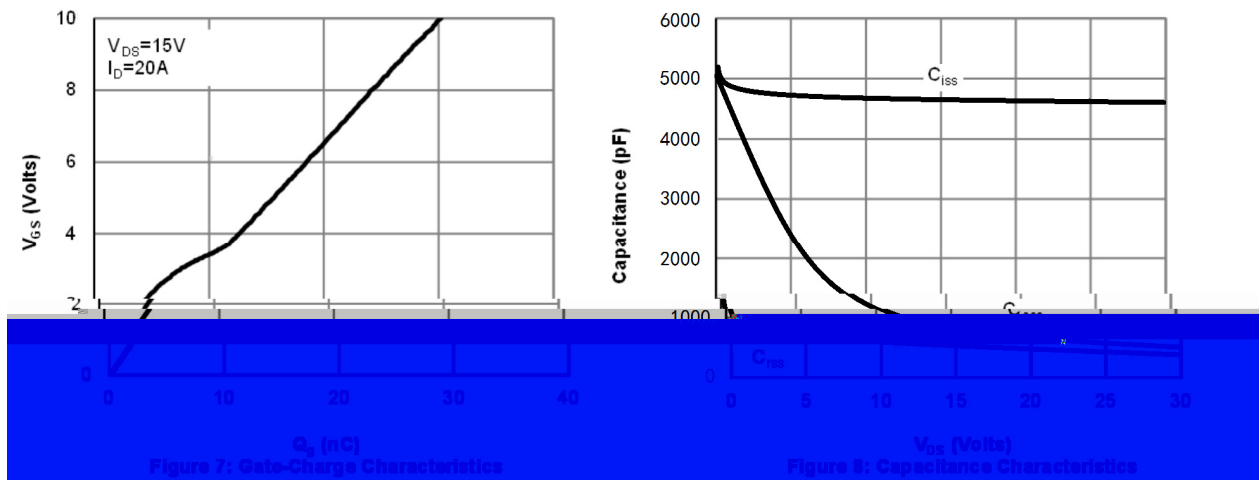
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=15V$ $I_D=20A$		32		nC
Total Gate Charge	$Q_{g(4.5V)}$			15		
Gate Source Charge	Q_{gs}			5.2		
Gate Drain Charge	Q_{gd}			6.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75$ $R_{GEN}=3$		8.5		ns
Turn-On Rise Time	t_r			4.2		
Turn-Off Delay Time	$t_{d(off)}$			30		
Turn-Off Fall Time	t_f			5.7		

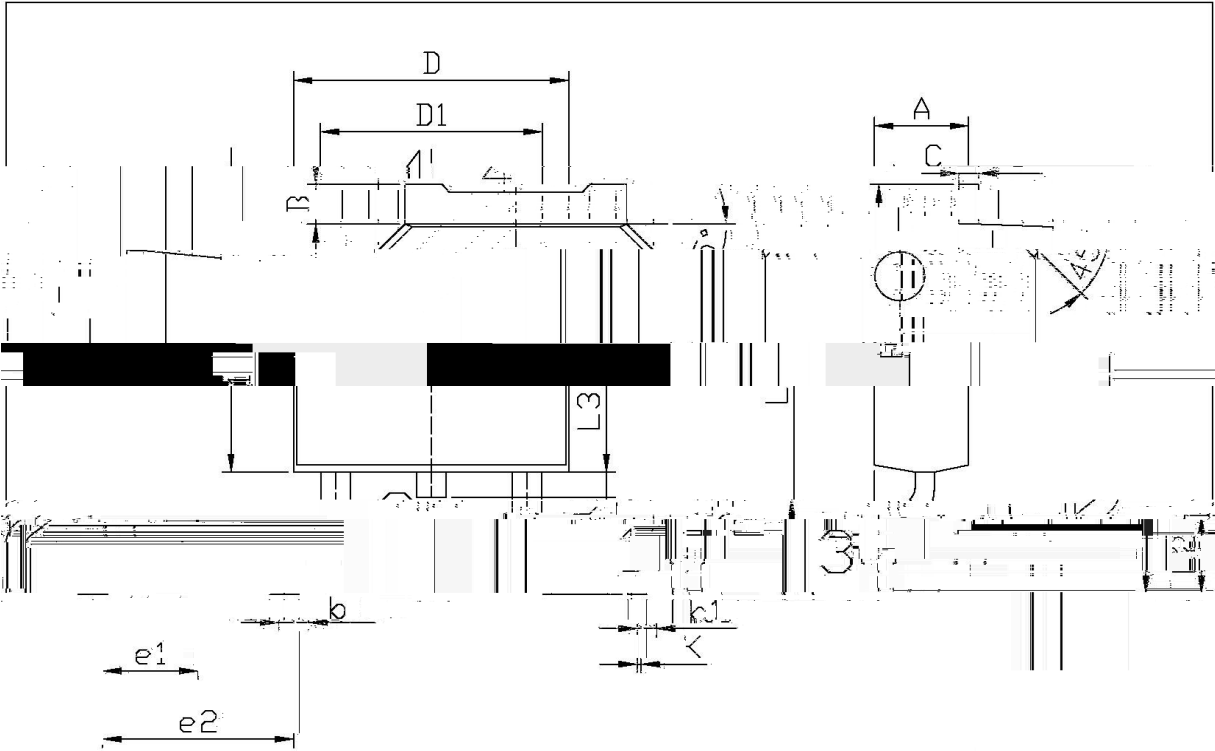
/ Electrical Characteristic Curve



/ Electrical Characteristic Curve



/ Package Dimensions



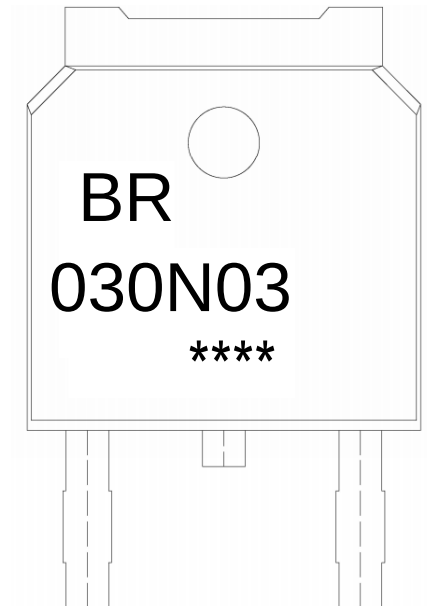
单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
6.25	A	2.20	2.40	E	5.95
2.34	B	0.95	1.25	e1	2.24
4.43	C	0.70	0.90	L3	0.45
9.85	D	10.35	5.11	D1	5.50
0.45	J2	1.70	2.00		
0.60		0.90			
0.00		0.10			

32

T0-25

/ Marking Instructions



BR

030N03

Note:

BR: Company Code

030N03: Product Type Code

****: Lot No. Code, code change with Lot No



() / **Temperature Profile for IR Reflow Soldering(Pb-Free)**

- 1

150 180

60 90sec;
- 2

245±5

5±0.5sec;
- 3

2 10

/sec.
- Note:

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.